

AMENDMENTS TO THE CLAIMS

1. (Original) A hexagonal boron nitride film having a specific inductance of 3.0 or less.
2. (Original) A hexagonal boron nitride film wherein the total number of the bonds between nitrogen and hydrogen atoms and between boron and hydrogen atoms is 4 mol% or less.
3. (Original) A hexagonal boron nitride film wherein a spacing in the c-axis direction is extended by 5 to 30% from 3.3 angstroms but the extension of a spacing in the a-axis direction is limited within 5% from 2.2 angstroms.
4. (Original) A hexagonal boron nitride film wherein the direction of the c-axis is parallel to a substrate.
5. (Original) A layer dielectric film comprising a hexagonal boron nitride film having a specific inductance of 3.0 or less.
6. (Original) The layer dielectric film according to claim 5, wherein the hexagonal boron nitride contains 40 mol% or less of amorphous boron nitride, 40 mol% or less of cubic boron nitride or 40 mol% or less of amorphous boron nitride and cubic boron nitride.
7. (Original) A layer dielectric film comprising a hexagonal boron nitride film wherein the total number of the bonds between nitrogen and hydrogen atoms and between boron and hydrogen atoms is 4 mol% or less.
8. (Original) The layer dielectric film according to claim 7, wherein the hexagonal boron nitride contains 40 mol% or less of amorphous boron nitride, 40 mol% or less of cubic boron nitride or 40 mol% or less of amorphous boron nitride and cubic boron nitride.
9. (Original) A layer dielectric film comprising a hexagonal boron nitride film wherein a spacing in the c-axis direction is extended by 5 to 30% from 3.3 angstroms but the extension of a spacing in the a-axis direction is limited within 5% from 2.2 angstroms.

10. (Original) The layer dielectric film according to claim 9, wherein the hexagonal boron nitride contains 40 mol% or less of amorphous boron nitride, 40 mol% or less of cubic boron nitride or 40 mol% or less of amorphous boron nitride and cubic boron nitride.

11. (Original) A layer dielectric film comprising a hexagonal boron nitride film wherein the direction of the c-axis is parallel to a substrate.

12. (Currently Amended) The layer dielectric film according to claim ~~10~~ 11, wherein the hexagonal boron nitride contains 40 mol% or less of amorphous boron nitride, 40 mol% or less of cubic boron nitride or 40 mol% or less of amorphous boron nitride and cubic boron nitride.

13. (Original) A method of producing a hexagonal boron nitride film by using an ion deposition method involving the radiation of a mixed ion consisting of a nitrogen ion or nitrogen and rare gas and the deposition of a boron supply source under vacuum, the method comprising using a nitrogen supply source and a boron supply source containing no bond with a hydrogen atom.

14. (Original) The method of producing a hexagonal boron nitride film according to claim 13, wherein the filming temperature of said substrate is designed to be 200 °C or less.

15. (Original) The method of producing a hexagonal boron nitride film according to claim 13, the method further comprising a step of introducing hydrogen by ion implantation.

16. – 18. (Canceled)